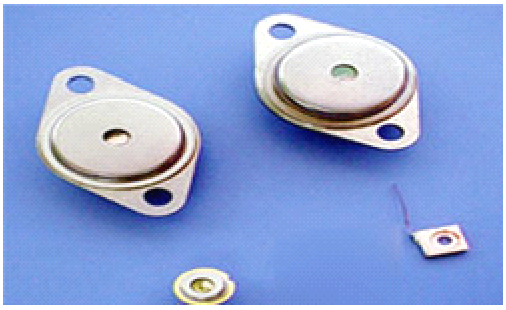
808 nm High-Power Laser Diode (AL808T1000)

Features:

Output power: 1w(CW)
Variety of stripe width
Efficient quantum well structure

Application:

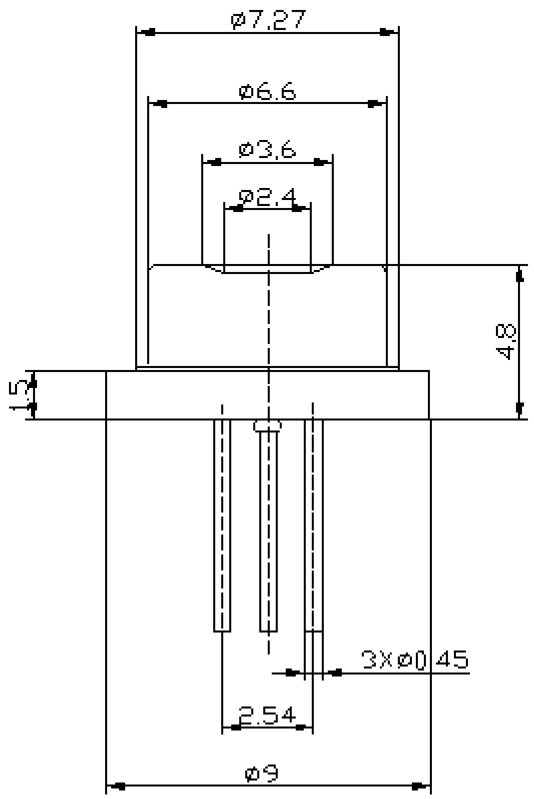
Solid-state laser pumping
Medical usage
Beacons and Illumination
Free-space communication
Infrared light sources



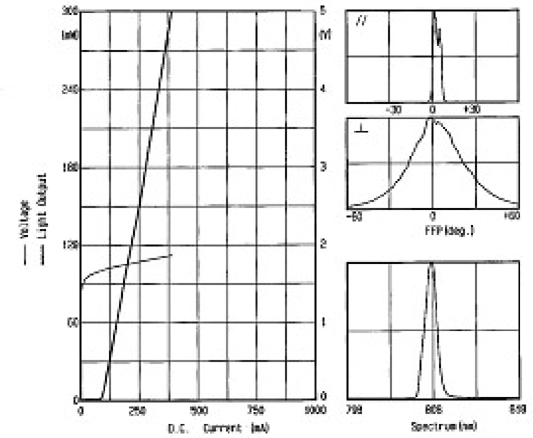
Specifications:

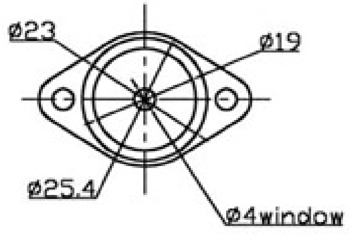
Parameter	Value
	AL808T1000
CW output power (mW)	1000
Peak wavelength (nm)	808±5
Spectral width (nm)	⩽5
Threshold current (A)	⩽200
Operating current (mA)	⩽1200
Operating voltage (V)	1. 8~2.2
Slope efficiency (W/A)	⩾0.9
Beam divergence $\theta_{\perp}\times\theta_{//}$ (deg.)	12/40
Wavelength temperature coefficient (nm/℃)	0.3
Emitting area (μm)	100×1
Serial resistance (Ω)	⩽1.5
Lifetime(h)	10000
Package	TO-5

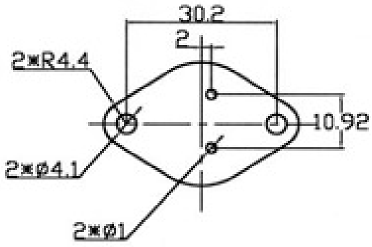
TO-5 Package：(Unit: mm)

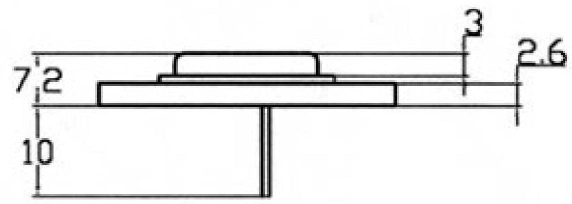


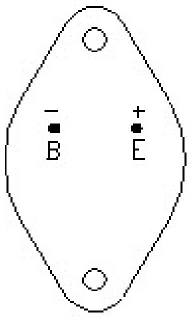
TO3 Packing

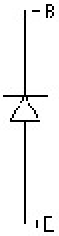












封装 **C-block Heat Sink：(Unit : mm，Heat Sink(+))**

C-block (C)